

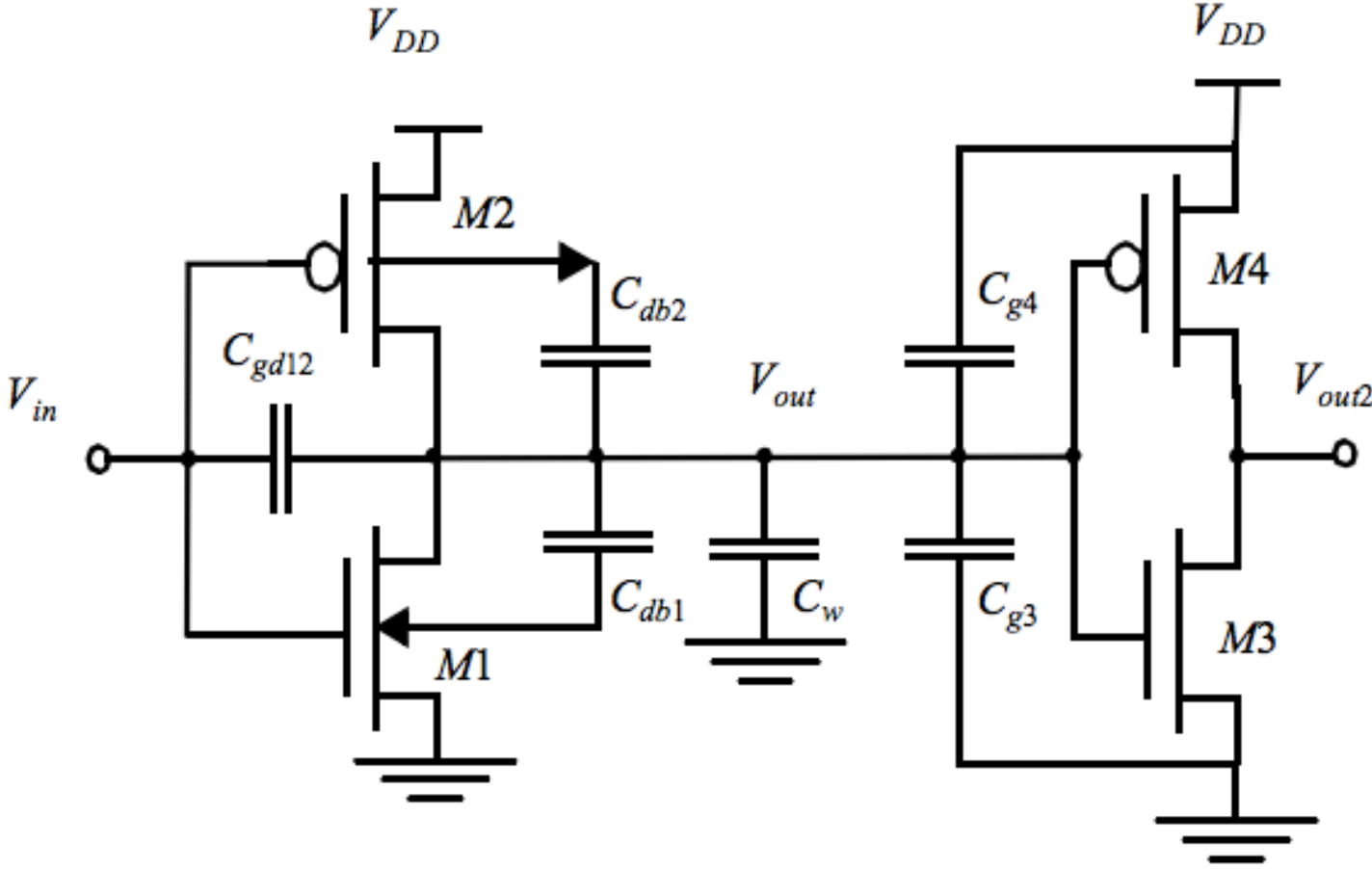
ESE370: Circuit-Level Modeling, Design, and Optimization for Digital Systems

Lec 14: October 8, 2021

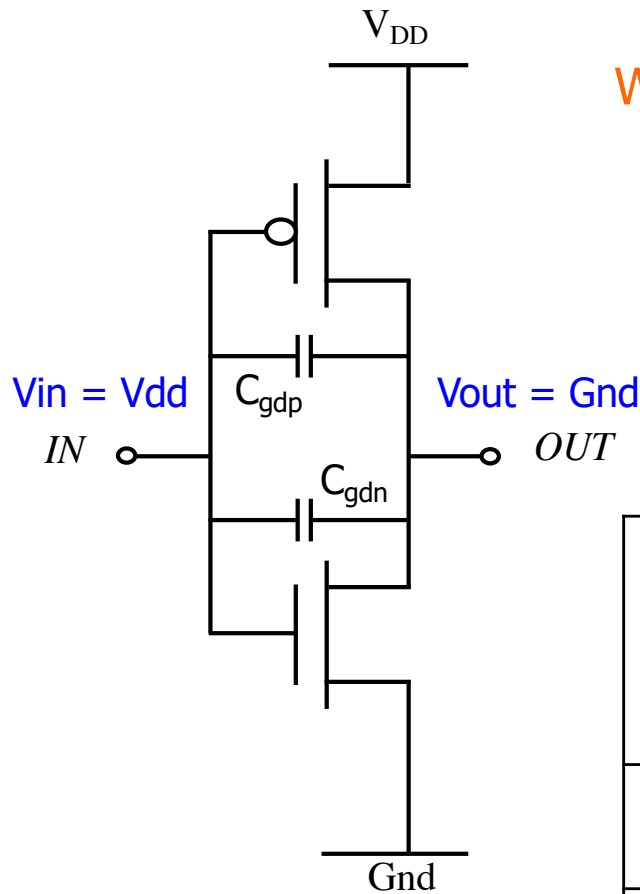
Performance: Gates



Capacitance Reminder



Charge on Capacitors (preclass 6)

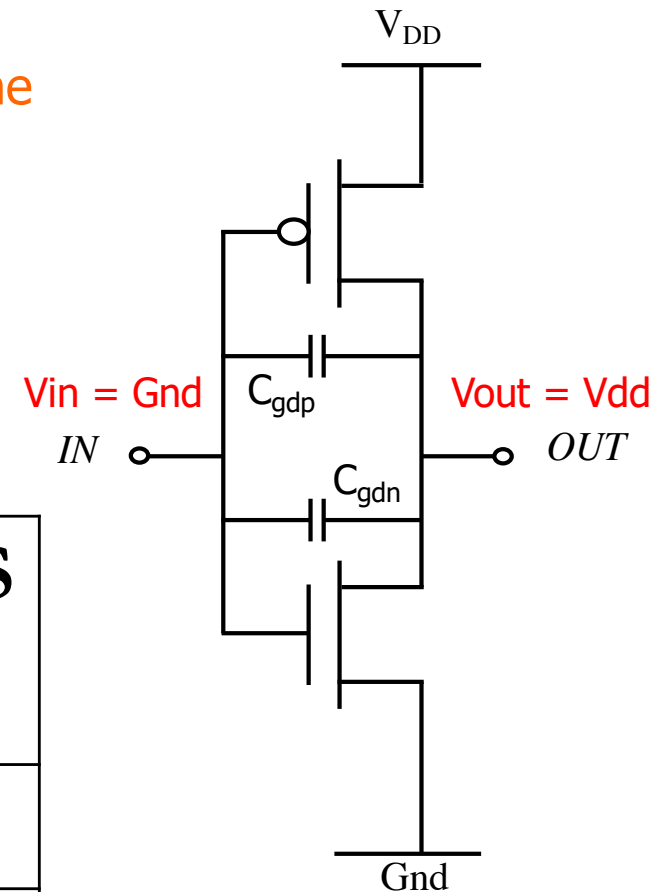


What is charge, Q , on each of the capacitors when $V_{in}=V_{dd}$ and $V_{in}=Gnd$?

	PMOS	NMOS
V_{in}	C_{gdp}	C_{gdn}
V_{dd}		
Gnd		

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V_{in}	C_{gdp}	C_{gdn}
V_{DD}		
Gnd		



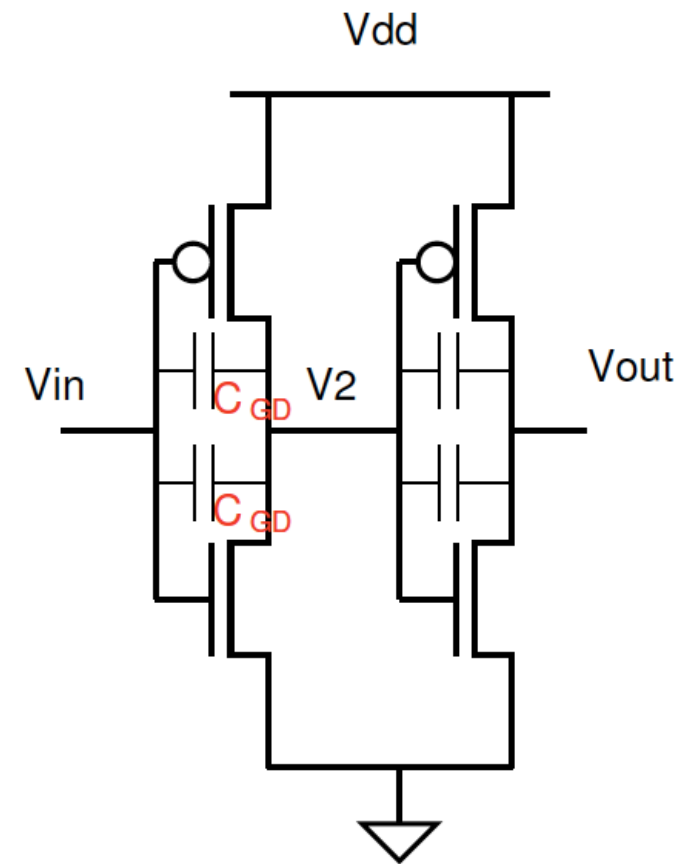
Questions

- ❑ What is ΔQ on each C_{gd} when input switched?
- ❑ Assuming $\Delta V = V_{dd}$, what is equivalent capacitance?

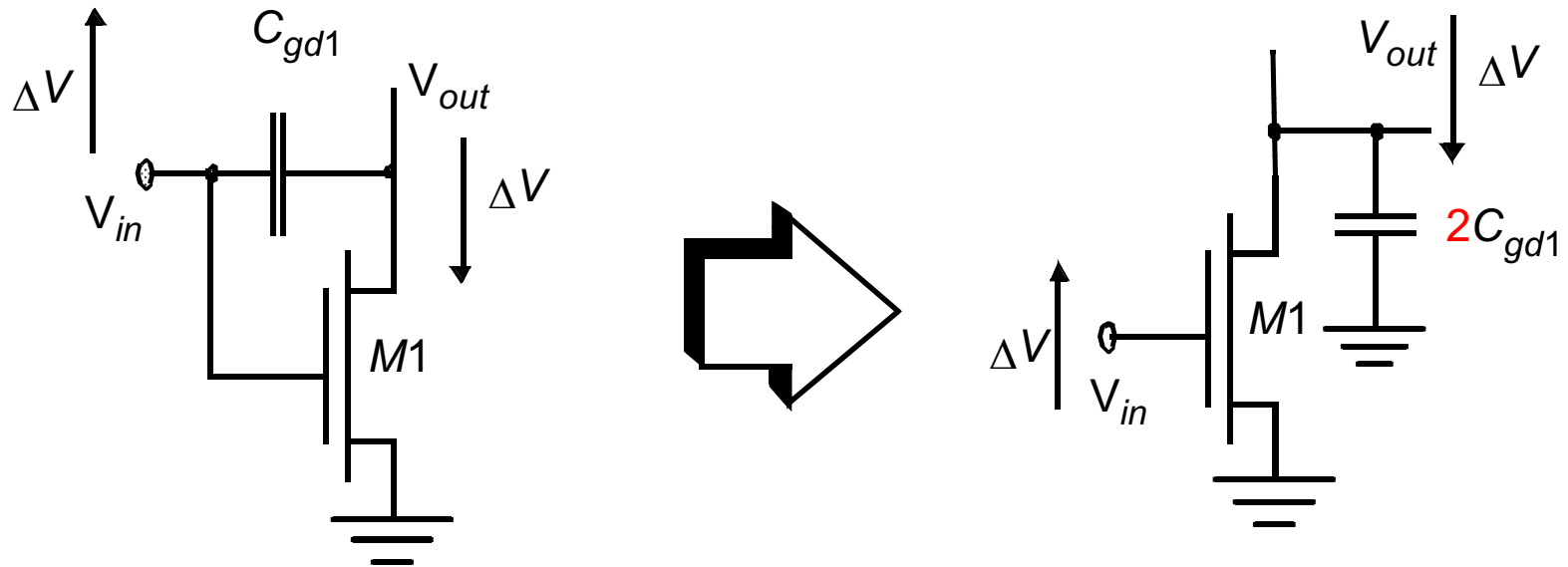
	PMOS	NMOS
V_{in}	C_{gdp}	C_{gdn}
V_{dd}		
Gnd		

Miller Effect For an Inverter

- ❑ Feedback capacitance (C_{gd}) between input and output must swing $2 V_{dd}$
- ❑ Or...behaves same as a double-sized capacitor on the output



Miller Effect For an Inverter



“A capacitor experiencing identical but opposite voltage swings at both its terminals can be replaced by a capacitor to ground, whose value is two times the original value.”



Previously: First Order Delay

- ❑ R_0 = Resistance of minimum size NMOS device
- ❑ $I_0 = I_{ds}$ of minimum size NMOS device
- ❑ C_0 = gate capacitance of minimum size NMOS device
- ❑ $R_{drive} = R_0/W_n$ $I_{drive} = W_n I_0$ $C_g = W_n C_0$
- ❑ Technology independent relative delay
$$\tau = R_0 C_0 = C_0 / I_0$$
- ❑ Large fanout results in large delays
 - Drive in stages to reduce delay



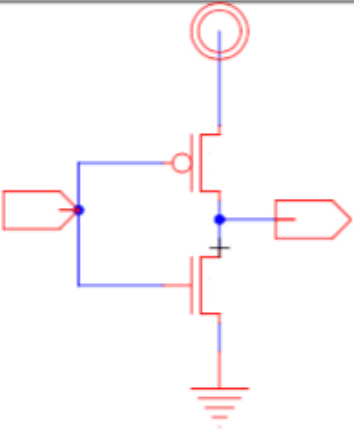
Today

- ❑ Delay in Gates
- ❑ Data Dependent Delay
- ❑ Large Fanin

- ❑ Analyze everything for two cases:
 - Ratio to minimize average delay: $R_{p0} = 2R_{n0} = 2R_0$
 - Extreme velocity saturation: $R_{p0} = R_{n0} = R_0$
 - Simplified case from Monday in analyzing fanout delays

Inverter Performance (preclass 1, row 1)

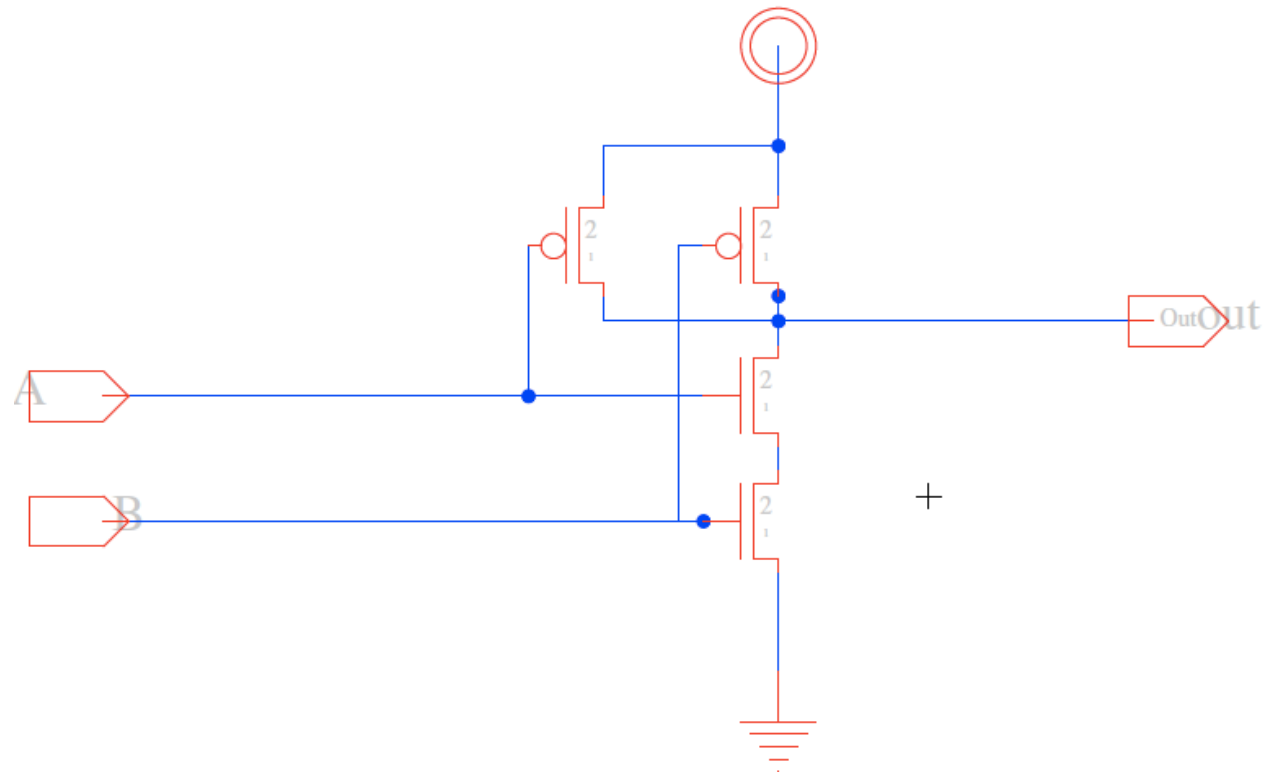
- Sized for $R_0/2$ drive resistance, ($R_0=R_{n0}$)

	$R_{p0} = R_{n0}$			$R_{p0} = 2R_{n0}$		
	W_p	W_n	C_a	W_p	W_n	C_a
	2	2	$4C_0$	4	2	$6C_0$



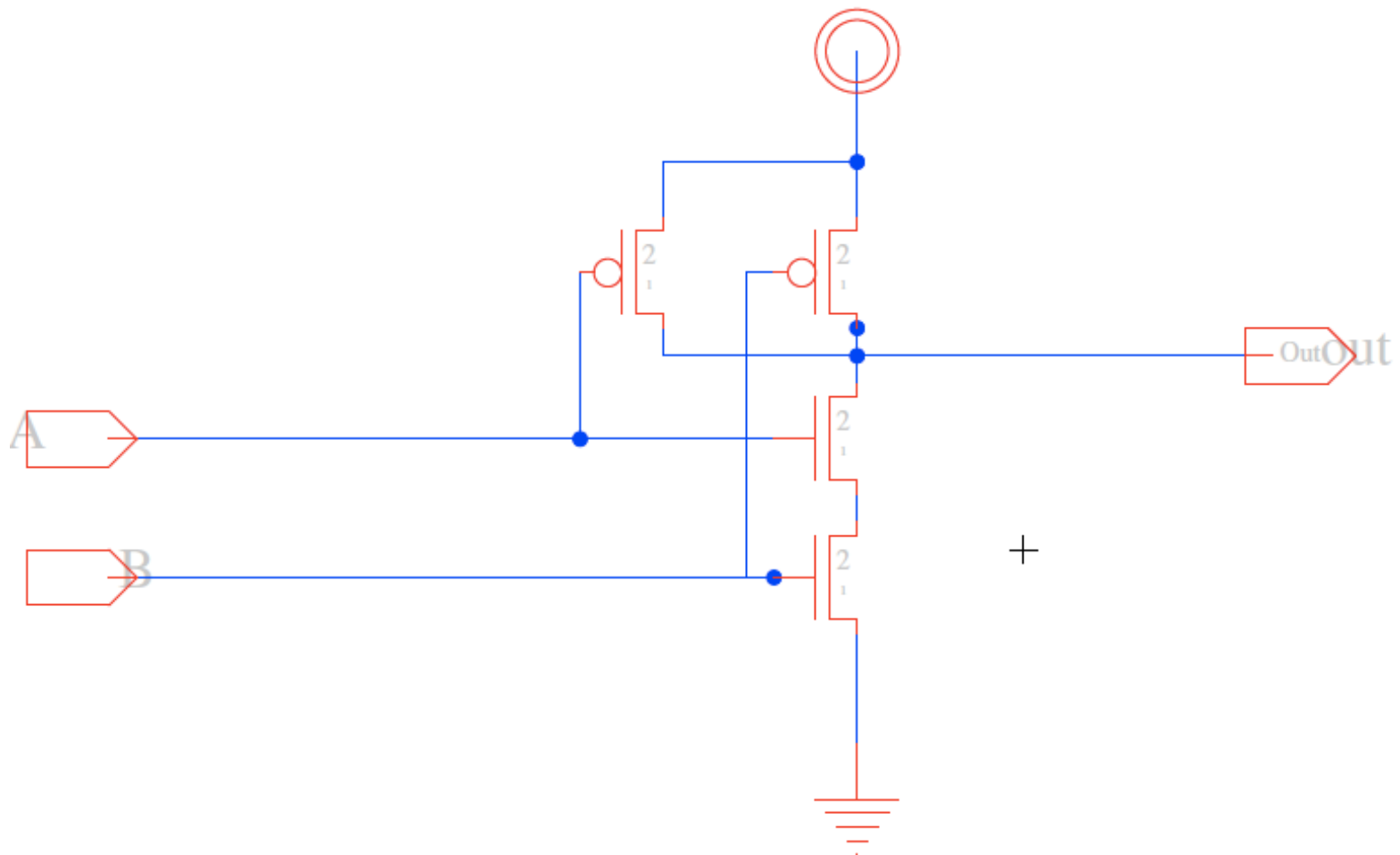
Data Dependent Delay

- ❑ Drive resistance depends on input values
 - Delay depends on input data
 - Analyze using worst case delay



Transistor Sizing (preclass 1, row 2)

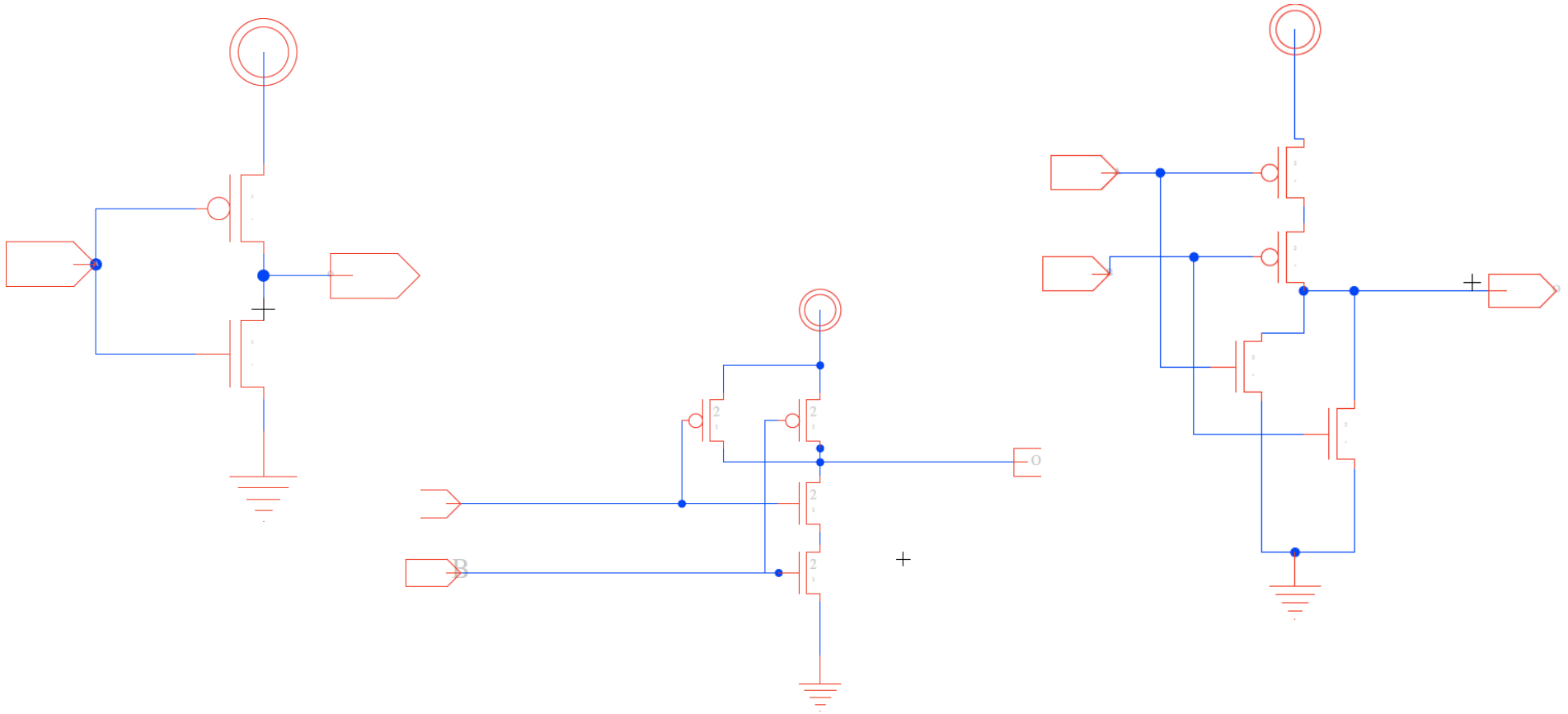
- How should we size to equalize worst-case rise/fall times for $R_{\text{drive}} = R_0/2$?





Input Load

- Input capacitance per input in each case?



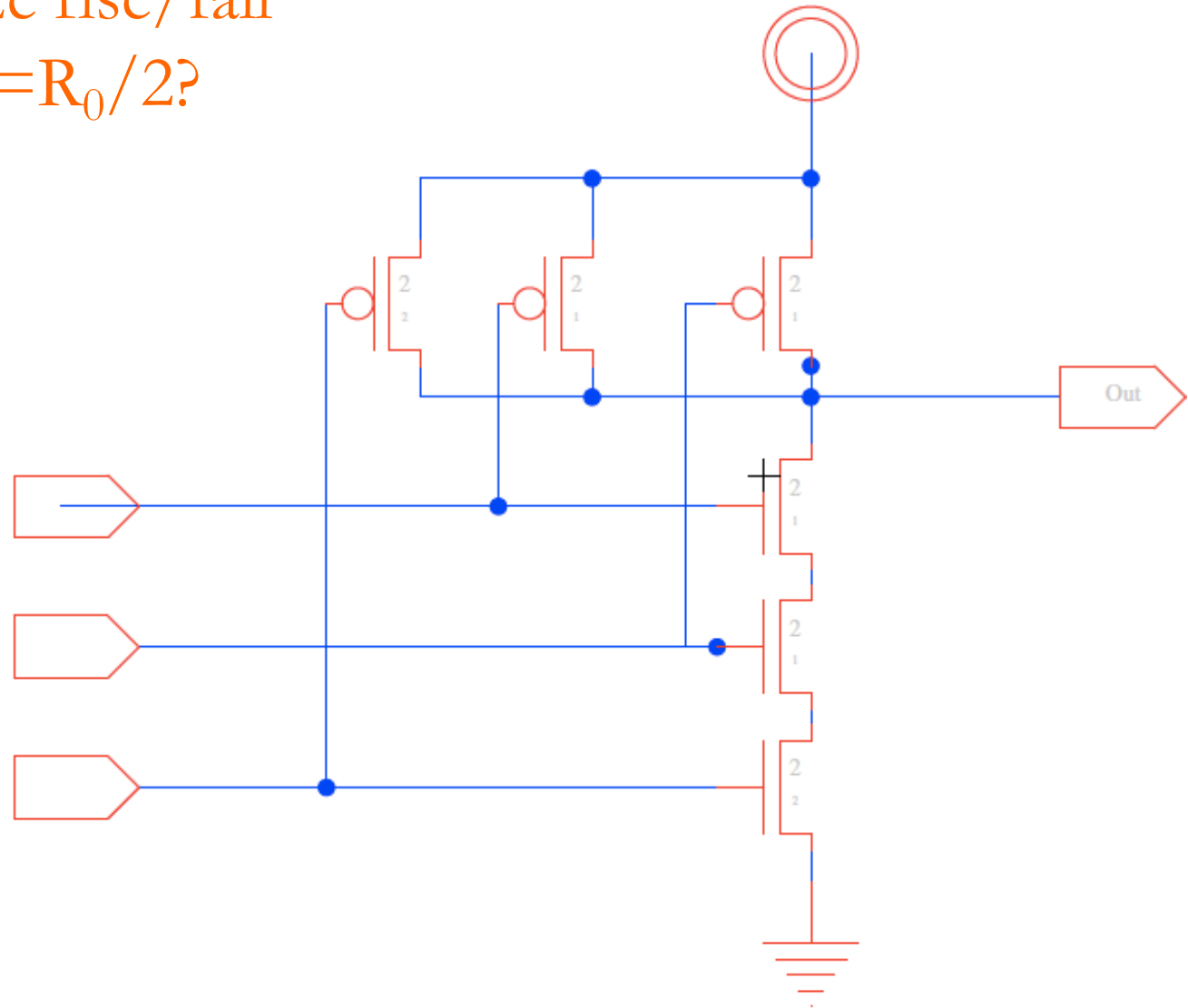


Observe

- Ratio of Input Load Capacitance to Output Drive Strength: $C_{\text{InLoad}}/I_{\text{ds}}$
 - Differs with gate function
 - Gate efficiency

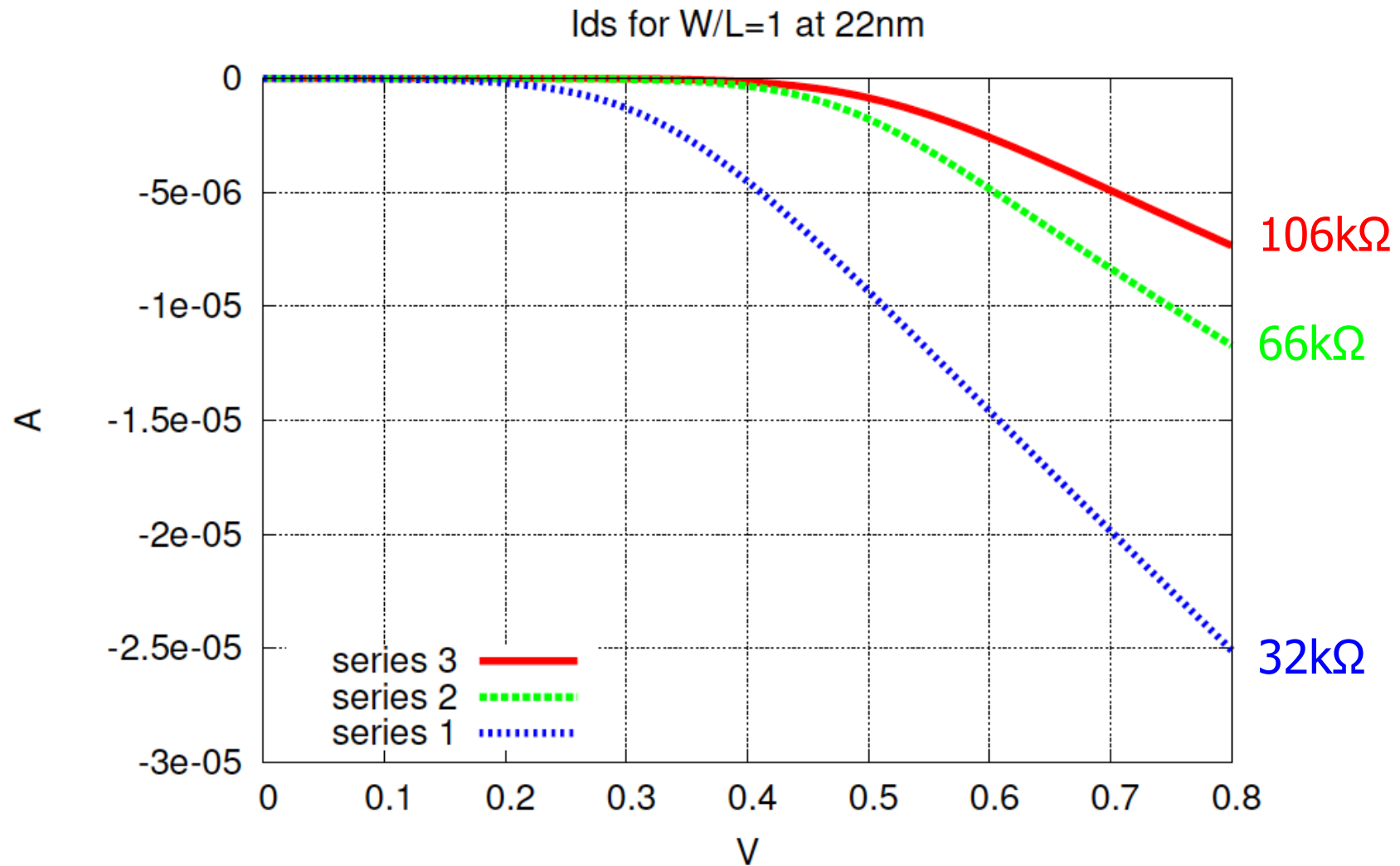
Transistor Sizing (preclass 1, row 4)

- Size equalize rise/fall times $R_{drive} = R_0/2?$





Series Transistors





Increasing Fanin (preclass 2)

- What happens to input capacitance as fanin (k) increases
 - Keeping output drive the same
 - E.g. $R_{\text{drive}} = R_0/2$
- k -input nand gate has what input capacitance?



Fanin

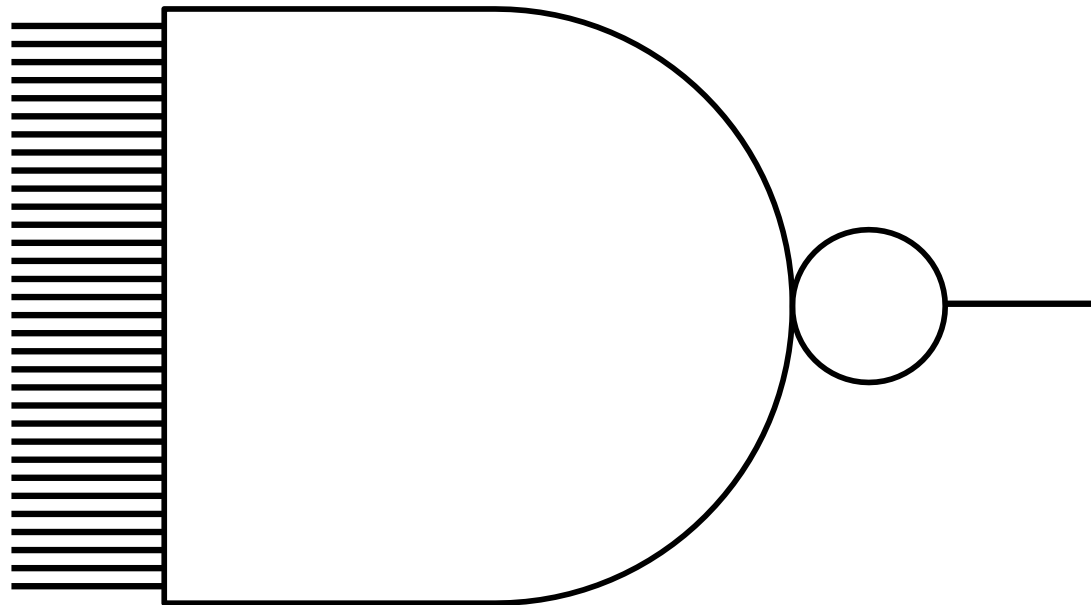
- **Conclude:** gates slow down with fanin
 - Less drive per input capacitance
 - $C_{\text{InLoad}}/I_{\text{ds}}$ increases

nand32 (preclass 3, row 1)

- single-stage nand32

$R_{n0} = R_{p0}$ case only

- Delay with $R_0/2$ input drive and $4C_0$ load?

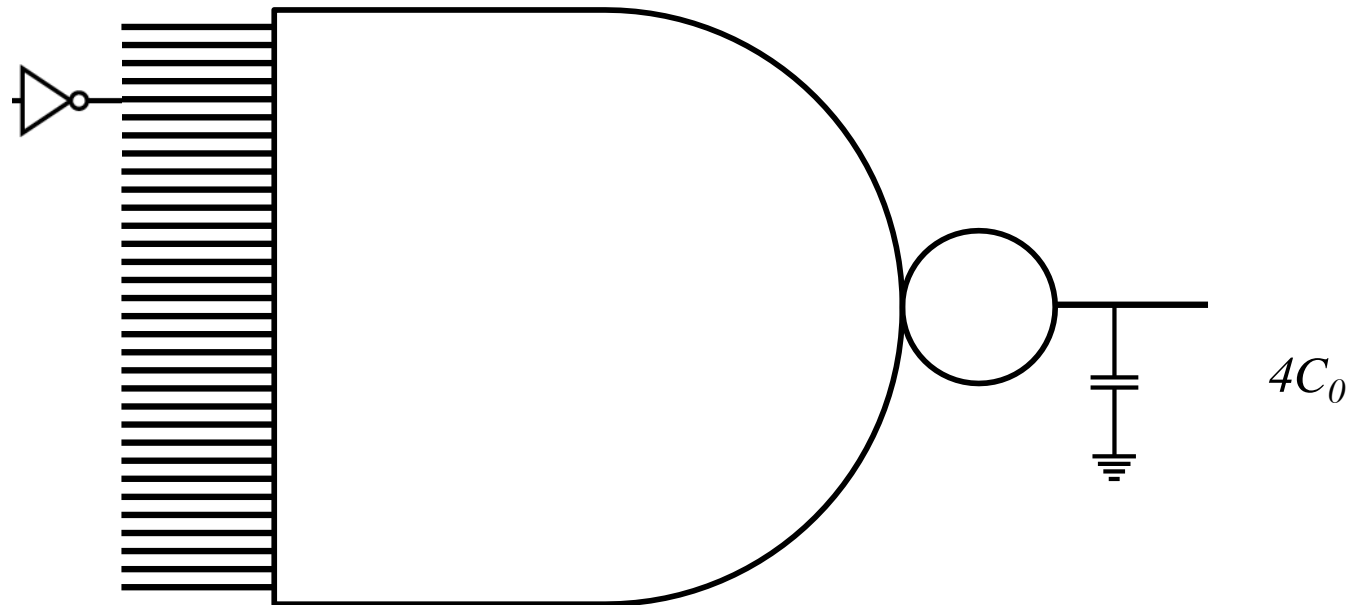


nand32 (preclass 3, row 1)

□ nand32

$R_{n0} = R_{p0}$ case only

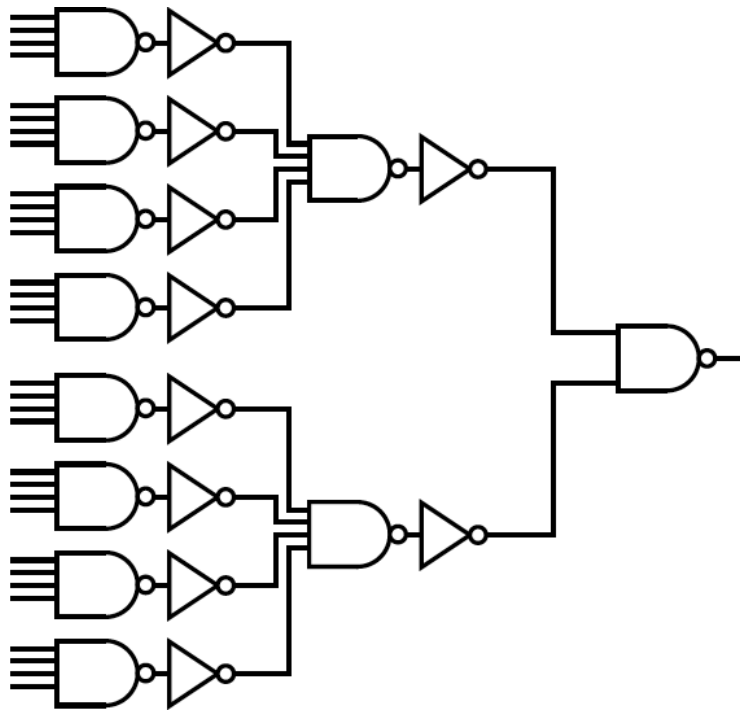
- Delay with $R_0/2$ input drive and $4C_0$ load?



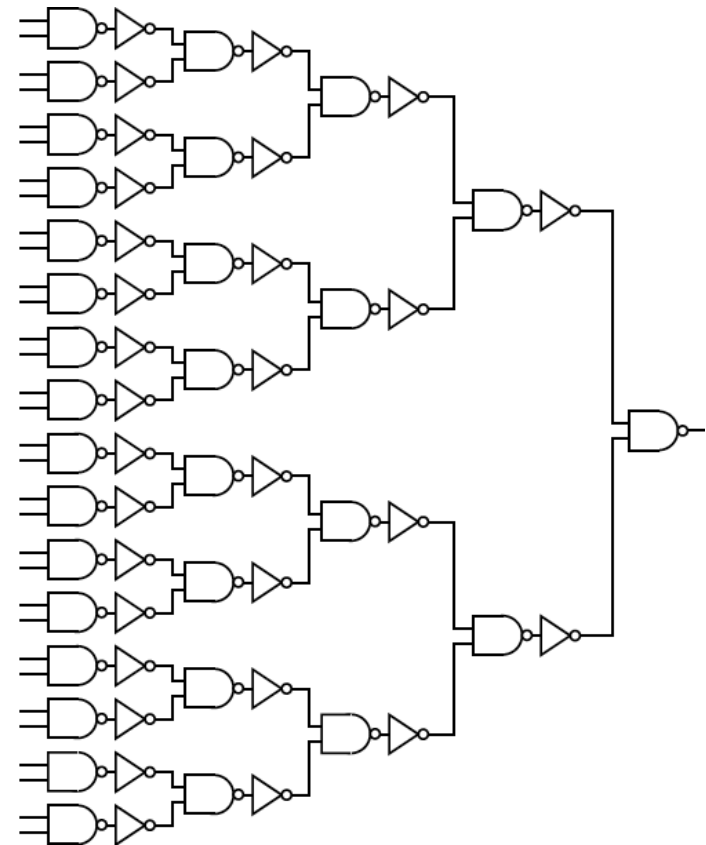
Which is Faster? (preclass 3, rows 2&3)

□ nand32

$R_{n0} = R_{p0}$ case only



nand4-inv-nand4-inv-nand2



$(\text{nand2-inv})^4\text{-nand2}$

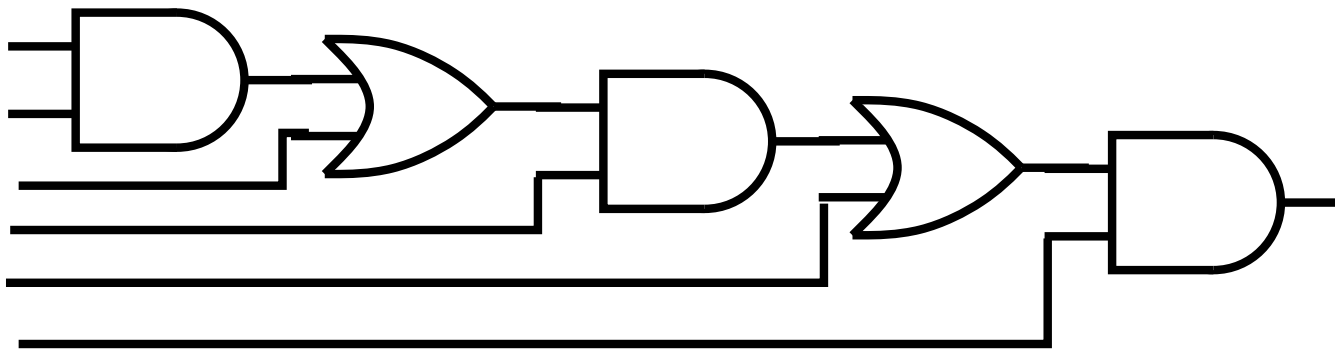


Lesson

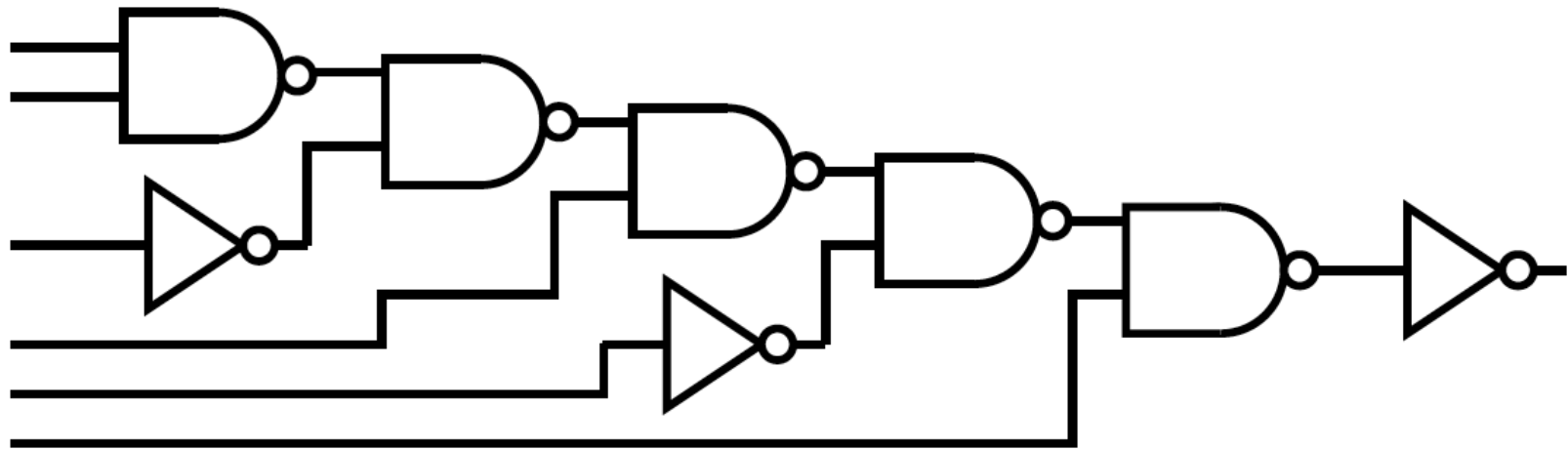
- ❑ Large gates are slow / inefficient
 - High capacitive load / drive current
- ❑ Small gates can be inefficient
 - Need many stages
- ❑ Staging over moderate size gates minimizes delay
- ❑ Exact size will be technology dependent



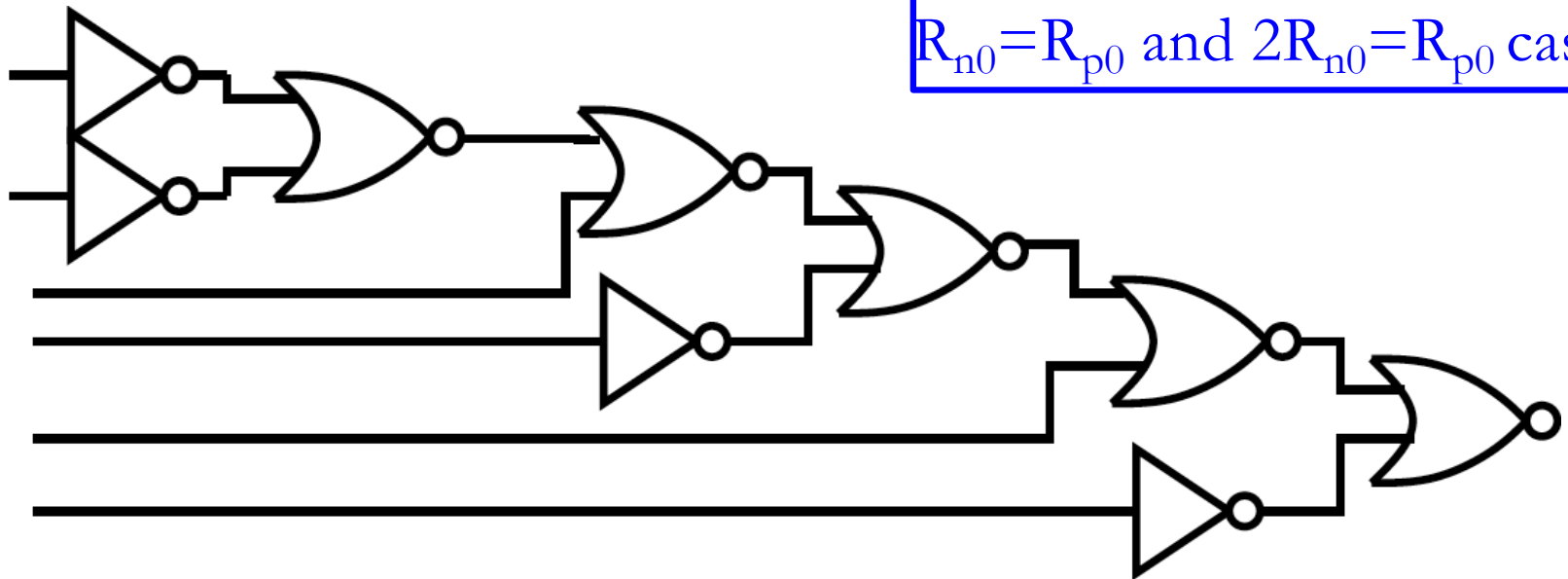
And-Or Chain



Delay of each implementation? (preclass 4)



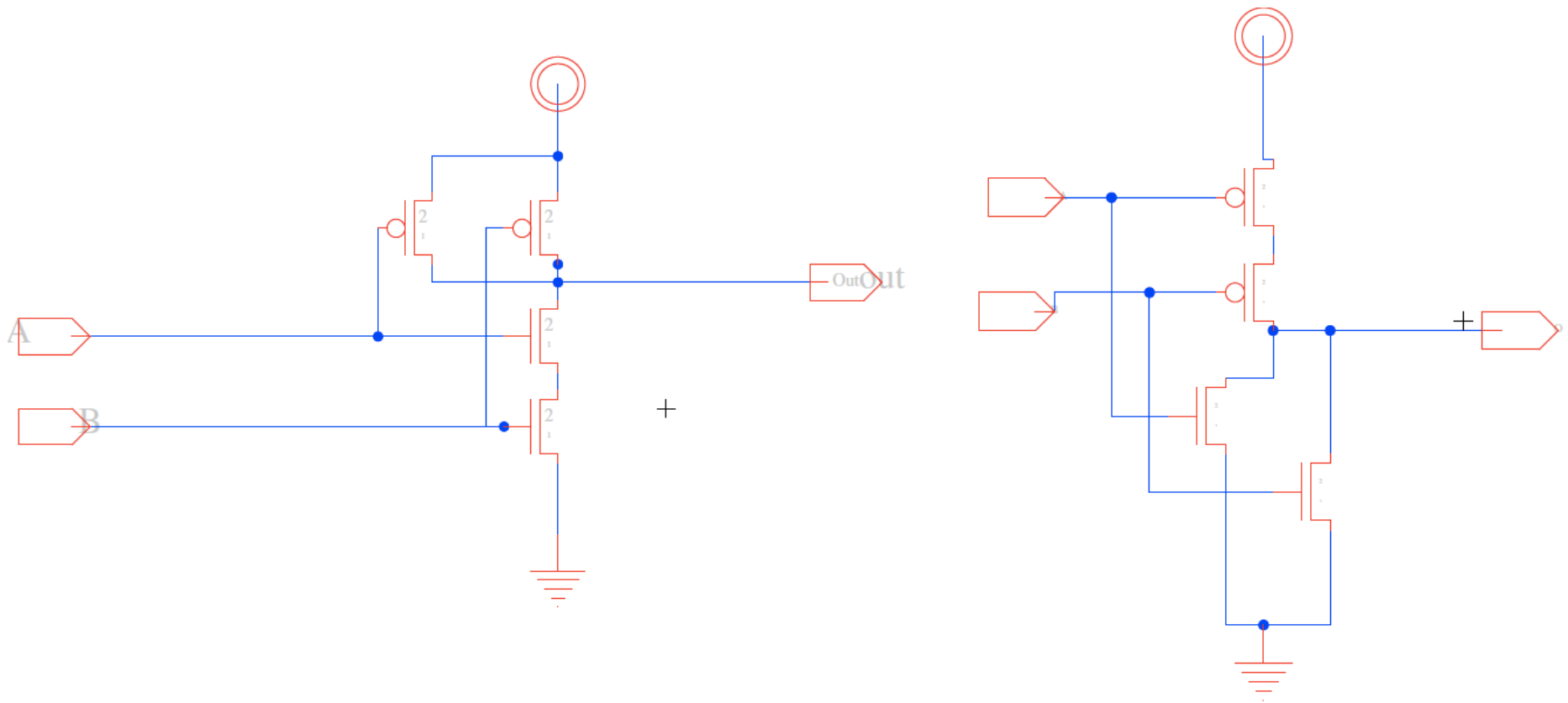
$R_{n0} = R_{p0}$ and $2R_{n0} = R_{p0}$ cases





Take Away?

- ❑ nor vs. nand





Ideas

- ❑ First order reason in $\tau = R_0C_0$ units
- ❑ Gates have different efficiencies
 - Drive strength per unit input capacitance
- ❑ Without velocity saturation
 - Reason to prefer nand over nor
- ❑ With velocity saturation
 - nands and nors are similar efficiency
- ❑ Large fanin and fanout slow gates
 - Decompose into stages
 - ...but not too many



Admin

- HW 4
 - Due tonight at midnight
- HW 5 out now
 - Is long and will take time, start today
 - Due during fall break 10/15